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Editors

# Defects at Oxide Surfaces

 Springer

# Contents

<b>1</b>	<b>Numerical Simulations of Defective Structures: The Nature of Oxygen Vacancy in Non-reducible (MgO, SiO<sub>2</sub>, ZrO<sub>2</sub>) and Reducible (TiO<sub>2</sub>, NiO, WO<sub>3</sub>) Oxides . . . . .</b>	<b>1</b>
	Gianfranco Pacchioni	
1.1	Introduction: The Role of Defects in Oxide Materials . . . . .	1
1.2	Treating Defects in Solids: Periodic Models and Local Modes . . . . .	4
1.2.1	Periodic Models . . . . .	4
1.2.2	Local Cluster Models . . . . .	5
1.2.3	Embedding Schemes . . . . .	6
1.3	Problems of DFT in Describing Defects in Insulators: Some Instructive Examples . . . . .	8
1.4	The Oxygen Vacancy in Insulating and Semiconducting Oxides . . . . .	10
1.4.1	Non-reducible Oxides: SiO <sub>2</sub> , MgO, ZrO <sub>2</sub> . . . . .	11
1.4.2	Reducible Oxides: TiO <sub>2</sub> , NiO and WO <sub>3</sub> . . . . .	16
1.5	Conclusions . . . . .	22
	References. . . . .	24
<b>2</b>	<b>Atomic Scale Characterization of Defects on Oxide Surfaces. . . . .</b>	<b>29</b>
	Niklas Nilus, Martin Sterrer, Markus Heyde and Hans-Joachim Freund	
2.1	Introduction . . . . .	29
2.2	Point Defects . . . . .	30
2.2.1	Non-reducible Oxides: MgO . . . . .	30
2.2.2	Reducible Oxides . . . . .	48
2.3	Line Defects . . . . .	58
2.3.1	Dislocation Network in Alumina Thin Films . . . . .	58
2.3.2	Line Defects in MgO Thin Films . . . . .	63
2.3.3	Electron Trapping in MgO Line Defects . . . . .	66

2.4	Summary	70
	References	71
<b>3</b>	<b>Defects on TiO<sub>2</sub>—Key Pathways to Important Surface Processes</b>	<b>81</b>
	Zhen Zhang and John T. Yates Jr.	
3.1	Overview of Defects in Solids	81
3.1.1	0D Defects (Point Defects)	82
3.1.2	1D Defects (Line Defects)	85
3.1.3	2D Defects (Interfacial Defects)	86
3.1.4	3D Defects (Bulk Defects)	87
3.1.5	Defects on Surfaces	87
3.2	Crystal Forms of TiO <sub>2</sub>	88
3.3	Oxygen Point Defects	90
3.3.1	Oxygen Vacancy	90
3.3.2	Chemisorbed O <sub>i</sub> Defect	97
3.4	Ti Point Defects	100
3.5	H Point Defects on TiO <sub>2</sub>	102
3.5.1	OH/TiO <sub>2</sub>	103
3.5.2	Atomic H/TiO <sub>2</sub>	105
3.6	Doping of TiO <sub>2</sub>	107
3.7	Summary	109
	References	109
<b>4</b>	<b>Excess Electrons at Oxide Surfaces</b>	<b>123</b>
	Sylvie Bourgeois, Bruno Domenichini and Jacques Jupille	
4.1	Introduction	123
4.2	Rutile TiO <sub>2</sub> (110) Surface	124
4.2.1	Point Defects Versus Excess Charges	125
4.2.2	Spectroscopic Fingerprint of Excess Charges	126
4.2.3	Location of Excess Electrons	128
4.2.4	Excess Charges Located Independently of Their Origin	133
4.3	Adsorbates on Rutile (110)	134
4.3.1	Molecular and Dissociative Adsorption of Oxygen	134
4.3.2	Hydroxylated Sites	137
4.4	Anatase	139
4.4.1	Reduced Anatase	140
4.4.2	Defective Anatase (101) Surface	140
4.4.3	Negatively Charged Oxygen on Reduced Anatase (101)	143
4.5	Conclusion	144
	References	144

<b>5</b>	<b>Oxygen Defects at Reducible Oxide Surfaces: The Example of Ceria and Vanadia</b> . . . . .	149
	María Verónica Ganduglia-Pirovano	
5.1	Introduction . . . . .	149
5.2	Models and Computational Methods . . . . .	151
5.2.1	Point Defect Modeling . . . . .	151
5.2.2	Electronic Structure Methods . . . . .	152
5.2.3	Defect Formation Energy and Statistical Thermodynamics . . . . .	155
5.3	Cerium Oxide . . . . .	156
5.3.1	Experimental Findings on Oxygen Defects. . . . .	157
5.3.2	Structure Relaxation and Electronic Structure. . . . .	158
5.3.3	Defect Stability . . . . .	163
5.3.4	Summary of Cerium Oxide . . . . .	169
5.4	Vanadium Oxide . . . . .	170
5.4.1	Experimental Findings on Oxygen Defects. . . . .	171
5.4.2	Structure Relaxation and Electronic Structure. . . . .	172
5.4.3	Defect Stability . . . . .	176
5.4.4	Summary Vanadium Oxide . . . . .	180
5.5	Summary and Outlook . . . . .	181
	References. . . . .	183
<b>6</b>	<b>The Structure and Properties of Clean Steps at Oxide Surfaces</b> . . . . .	191
	Matthew J. Wolf and Alexander L. Shluger	
6.1	Introduction . . . . .	191
6.2	The Atomic Structure of Steps . . . . .	193
6.3	Understanding and Predicting Step Stabilities. . . . .	199
6.3.1	Calculation of the Step Stability . . . . .	199
6.3.2	Surface Morphologies from Step Formation Energies. . . . .	202
6.4	The Electronic Structure of Steps . . . . .	205
6.5	Point Defects at Steps . . . . .	208
6.6	Outlook. . . . .	210
	References. . . . .	211
<b>7</b>	<b>Defects on Bulk MgO(001) Imaged by nc-AFM</b> . . . . .	215
	Clemens Barth	
7.1	Introduction . . . . .	215
7.2	Electrostatic AFMs . . . . .	215
7.2.1	Principles of EFM and KPFM . . . . .	216
7.2.2	Charged Defects in EFM and KPFM. . . . .	219

7.3	Magnesium Oxide Surfaces . . . . .	220
7.3.1	Bulk MgO(001) Surfaces . . . . .	221
7.3.2	Summary and Perspectives . . . . .	232
	References . . . . .	234
<b>8</b>	<b>Noncontact AFM Imaging of Atomic Defects on the Rutile TiO<sub>2</sub>(110) Surface . . . . .</b>	<b>241</b>
	Jeppe V. Lauritsen	
8.1	Introduction . . . . .	241
8.2	Noncontact Atomic Force Microscopy . . . . .	242
8.2.1	Principle of Noncontact Atomic Force Microscopy . . . . .	243
8.2.2	Contrast Formation in Noncontact AFM Images . . . . .	244
8.2.3	Noncontact AFM Image Simulations . . . . .	247
8.3	Defects on Rutile TiO <sub>2</sub> (110) Studied with Noncontact AFM . . . . .	249
8.3.1	The Rutile TiO <sub>2</sub> (110) Surface and Its Surface Defects . . . . .	250
8.3.2	Noncontact AFM Contrast on the Rutile TiO <sub>2</sub> (110) Surface . . . . .	253
8.3.3	Tip Influence on the nc-AFM Contrast on the Rutile TiO <sub>2</sub> (110) Surface . . . . .	257
8.3.4	Force Spectroscopy on the Rutile TiO <sub>2</sub> (110) Surface . . . . .	259
8.3.5	Water Splitting Products, H Diffusion and Subsurface H on the TiO <sub>2</sub> (110) Surface . . . . .	262
8.3.6	Summary and Perspectives . . . . .	265
	References . . . . .	266
<b>9</b>	<b>Defects in Metal Oxide Nanoparticle Powders . . . . .</b>	<b>273</b>
	Thomas Berger and Oliver Diwald	
9.1	Introduction . . . . .	273
9.1.1	Particle Systems and the Hierarchy of Defects . . . . .	273
9.1.2	Stoichiometry, Levels of Oxygen Deficiency and <i>n</i> -Type Doping . . . . .	278
9.2	Experimental Probes for Defects in Nanoparticle Ensembles . . . . .	280
9.2.1	Materials Characterization for Powder Systems: Inherent Challenges, Faults and the Requirement for an Integrated Approach . . . . .	280
9.2.2	Point Defects and Experimental Fingerprints . . . . .	280

9.3	The Quest for Morphologically Defined Particle Systems . . . . .	285
9.3.1	Science of Synthesis . . . . .	285
9.3.2	MgO Powders as Model System for Highly Dispersed Solids . . . . .	285
9.3.3	Particle Interfaces and the Microstructure of Powders . . . . .	287
9.3.4	Powders of Facetted TiO <sub>2</sub> Particles . . . . .	288
9.4	Summary and Outlook . . . . .	292
	References . . . . .	293
<b>10</b>	<b>Point Defects in Electron Paramagnetic Resonance . . . . .</b>	<b>303</b>
	Elio Giamello, Mario Chiesa and Maria Cristina Paganini	
10.1	Introduction . . . . .	303
10.2	The EPR Techniques: A Summary . . . . .	304
10.2.1	The Spin-Hamiltonian Formalism . . . . .	304
10.2.2	Single Crystal Systems . . . . .	306
10.2.3	Polycrystalline Systems . . . . .	307
10.3	Colour Centres in the Bulk of Ionic Solids . . . . .	308
10.4	Localized Holes and V Centers in Ionic Solids . . . . .	311
10.5	Surface Defects as Electron Traps: A Paradigm Shift . . . . .	312
10.6	Surface Trapping Sites for Charge Carriers . . . . .	318
10.6.1	Insulating Ionic Oxides . . . . .	319
10.6.2	Semiconducting Oxides . . . . .	323
10.7	Conclusions . . . . .	324
	References . . . . .	324
<b>11</b>	<b>Defects on Strontium Titanate . . . . .</b>	<b>327</b>
	Matthew S.J. Marshall, Andres E. Becerra-Toledo, Laurence D. Marks and Martin R. Castell	
11.1	Introduction . . . . .	327
11.2	Defects in Bulk SrTiO <sub>3</sub> . . . . .	328
11.2.1	Point Defects . . . . .	328
11.2.2	Vacancy Clusters . . . . .	329
11.2.3	Ruddlesden-Popper Phases . . . . .	330
11.2.4	Dislocations and Defects . . . . .	331
11.2.5	Defects Introduced by Ar-Bombardment . . . . .	331
11.3	Surfaces of SrTiO <sub>3</sub> . . . . .	333
11.3.1	Surface Structure of SrTiO <sub>3</sub> (001) . . . . .	333
11.3.2	Polyhedral Quartet Structural Motif . . . . .	334
11.3.3	Nanostructured SrTiO <sub>3</sub> . . . . .	334
11.4	Surface Defects . . . . .	339
11.4.1	Defects at the Surface of SrTiO <sub>3</sub> . . . . .	339
11.4.2	Surface Vacancy Clusters . . . . .	339

11.4.3	Polyhedral Quartet Defects. . . . .	340
11.4.4	Triline Defects . . . . .	341
11.5	Defect Diffusion. . . . .	342
11.5.1	Point Defect Diffusion. . . . .	342
11.5.2	Diffusion of Defect Clusters. . . . .	342
11.6	Conclusions. . . . .	346
	References. . . . .	346
<b>12</b>	<b>Dopant and Defect Induced Electronic States at In<sub>2</sub>O<sub>3</sub> Surfaces . . . . .</b>	<b>351</b>
	Russell G. Egdell	
12.1	Introduction . . . . .	351
12.2	The Structure of In <sub>2</sub> O <sub>3</sub> and Its Surfaces. . . . .	352
12.2.1	Bulk Structure of In <sub>2</sub> O <sub>3</sub> . . . . .	352
12.2.2	Energetics of Surfaces and Surface Structures. . . . .	354
12.3	Bulk Electronic Structure. . . . .	358
12.3.1	Basic Features of Electronic Structure . . . . .	358
12.3.2	The Bulk Bandgap . . . . .	358
12.3.3	The Charge Neutrality Level in In <sub>2</sub> O <sub>3</sub> . . . . .	363
12.4	Defects and Doping . . . . .	365
12.4.1	Bulk Defect States . . . . .	365
12.4.2	Defects at Surfaces . . . . .	365
12.4.3	Bulk N-Type Doping: Chemical Aspects. . . . .	367
12.4.4	Bulk N-Type Doping: The Effective Mass and the Onset of Degeneracy in Doped In <sub>2</sub> O <sub>3</sub> . . . . .	368
12.4.5	Doping and Plasmons . . . . .	371
12.5	Materials Preparation. . . . .	374
12.6	Photoemission Studies of In <sub>2</sub> O <sub>3</sub> and Sn-Doped In <sub>2</sub> O <sub>3</sub> . . . . .	377
12.6.1	Nominally Undoped In <sub>2</sub> O <sub>3</sub> : Band Bending and Carrier Accumulation . . . . .	377
12.6.2	Electronic States in the Bulk Bandgap. . . . .	382
12.6.3	Dopant Induced Electronic States: Conduction Band Photoemission. . . . .	384
12.6.4	Satellite Structure in Core Level Photoemission of Doped Samples . . . . .	386
12.7	Summary and Outlook . . . . .	388
	References. . . . .	390
<b>13</b>	<b>Resistive Switching in Oxides . . . . .</b>	<b>401</b>
	A. Mehonic and A.J. Kenyon	
13.1	Introduction . . . . .	401
13.2	Classes of Resistive Switching . . . . .	403
13.3	Phenomenology of Filamentary Resistive Switching . . . . .	405

13.3.1	Electroforming . . . . .	407
13.3.2	Extrinsic Filamentary Resistive Switching . . . . .	408
13.3.3	Intrinsic Filamentary Resistive Switching . . . . .	409
13.4	Memristive Systems and Memristor Model . . . . .	412
13.5	Quantisation of Conductance . . . . .	415
13.6	Technological Considerations . . . . .	419
13.6.1	Switching Endurance . . . . .	421
13.6.2	Uniformity of Switching Voltages and Currents . . . . .	422
13.6.3	Data Retention . . . . .	423
13.6.4	The Need for Selection Elements . . . . .	423
	References . . . . .	424
<b>14</b>	<b>Photon-, Electron-, and Scanning Tunneling Microscopy-Induced Defects on Oxide Surfaces</b> . . . . .	<b>429</b>
	Chi Lun Pang and Geoff Thornton	
14.1	Introduction . . . . .	429
14.2	Photon-Induced Defects . . . . .	430
14.3	Electron-Induced Defects . . . . .	436
14.4	Scanning Tunneling Microscopy-Induced Defects . . . . .	441
14.5	Future Outlook . . . . .	446
	References . . . . .	447
<b>Index</b>	. . . . .	<b>453</b>